



Pre/de-emphasis buffer modeling with IBIS

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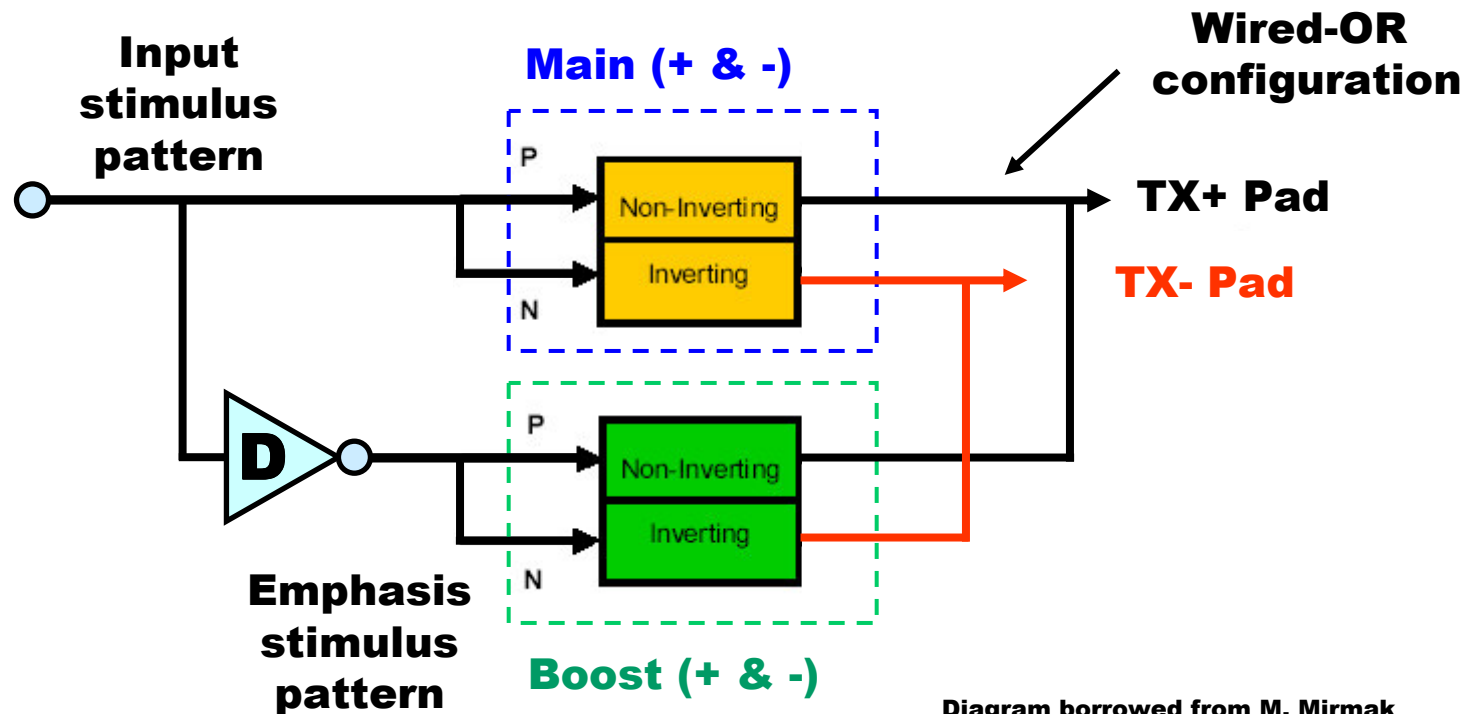
Options for modeling pre/de-emphasis buffers in IBIS

- **Model the building blocks of the buffer with independent [Model]s and tell the user to wire them up**
 - This approach was used initially for many models but required manual editing of files and/or simulation schematics
- **The legacy [Driver Schedule] keyword provides a reasonable solution to model pre/de-emphasis buffers**
 - <http://www.eda.org/pub/ibis/summits/jan05/muranyi.pdf>
 - Eliminates the need for manually connecting [Model]s to make a complete buffer
 - Uses no more than IBIS v3.2 syntax
 - Useful for tools not supporting the *-AMS extensions of IBIS
 - Reasonably good correlation with transistor level model
 - There are a few unsolved problems
- **The *-AMS language extensions of IBIS v4.1 provide means to solve the outstanding problems**
 - The issues around C_comp compensation can be solved
 - Switching into an unfinished edge, and
 - Data pattern dependent behavior can be added
 - Any other features and capabilities can be added as needed, such as
 - Frequency and/or voltage dependent C_comp, etc...

Pre/de-emphasis buffer review

In most of the current two-tap designs the “emphasis stimulus pattern” is a one bit delayed and inverted copy of the “input stimulus pattern”

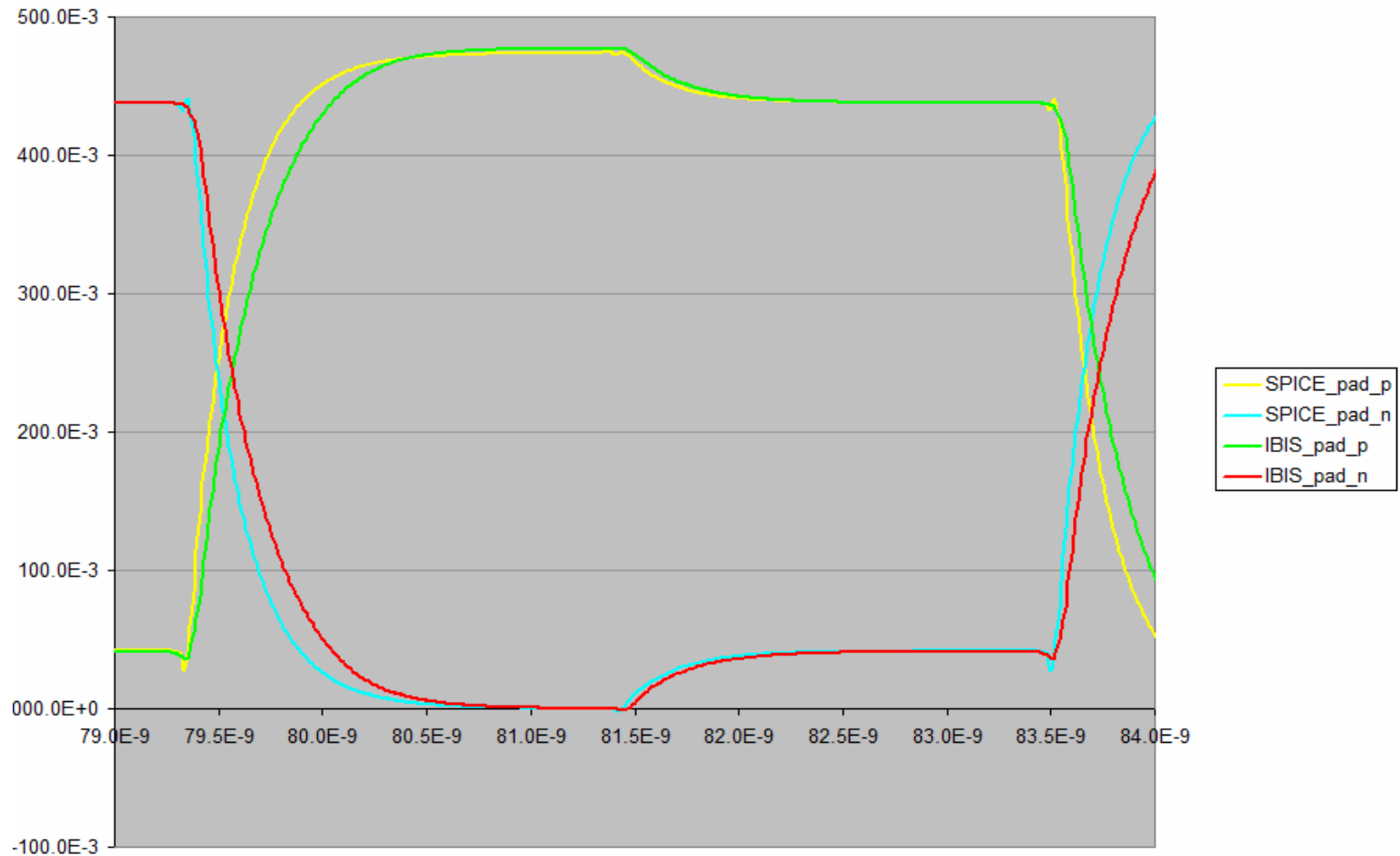
This is not necessarily true for all pre/de-emphasis buffer designs. The delay may not be a one bit duration in each design, and multi-tap configurations would usually have a more complicated stimulus logic.



C_comp issues

- **The IBIS specification says that C_comp should be placed into the “top level” model and should represent the total buffer capacitance**
- **This is easy for the model maker, but tool vendors need to answer some difficult questions:**
 - How is the C_comp compensation done?
 - independently, inside the Main and Boost [Model]s?
 - collectively?
 - If independently, how is the capacitive loading effect of the neighboring model(s) accounted for in the compensation algorithm?
 - How is the total C_comp divided between the Main and Boost buffers?
 - Is the C_comp compensation correct for each transition?
 - strong to strong bit
 - strong to weak bit
 - weak to strong bit
- **More C_comp related information:**
 - <http://www.eda.org/pub/ibis/summits/apr04/mirmak2.pdf>
 - <http://www.eda.org/pub/ibis/summits/oct04/mirmak2.pdf>
- **A constant C_comp value may not be accurate enough at GHz speeds**
 - Frequency and/or voltage dependence may be important, which can only be modeled with the IBIS v4.1 language extensions

Waveforms with independent C_comp compensation

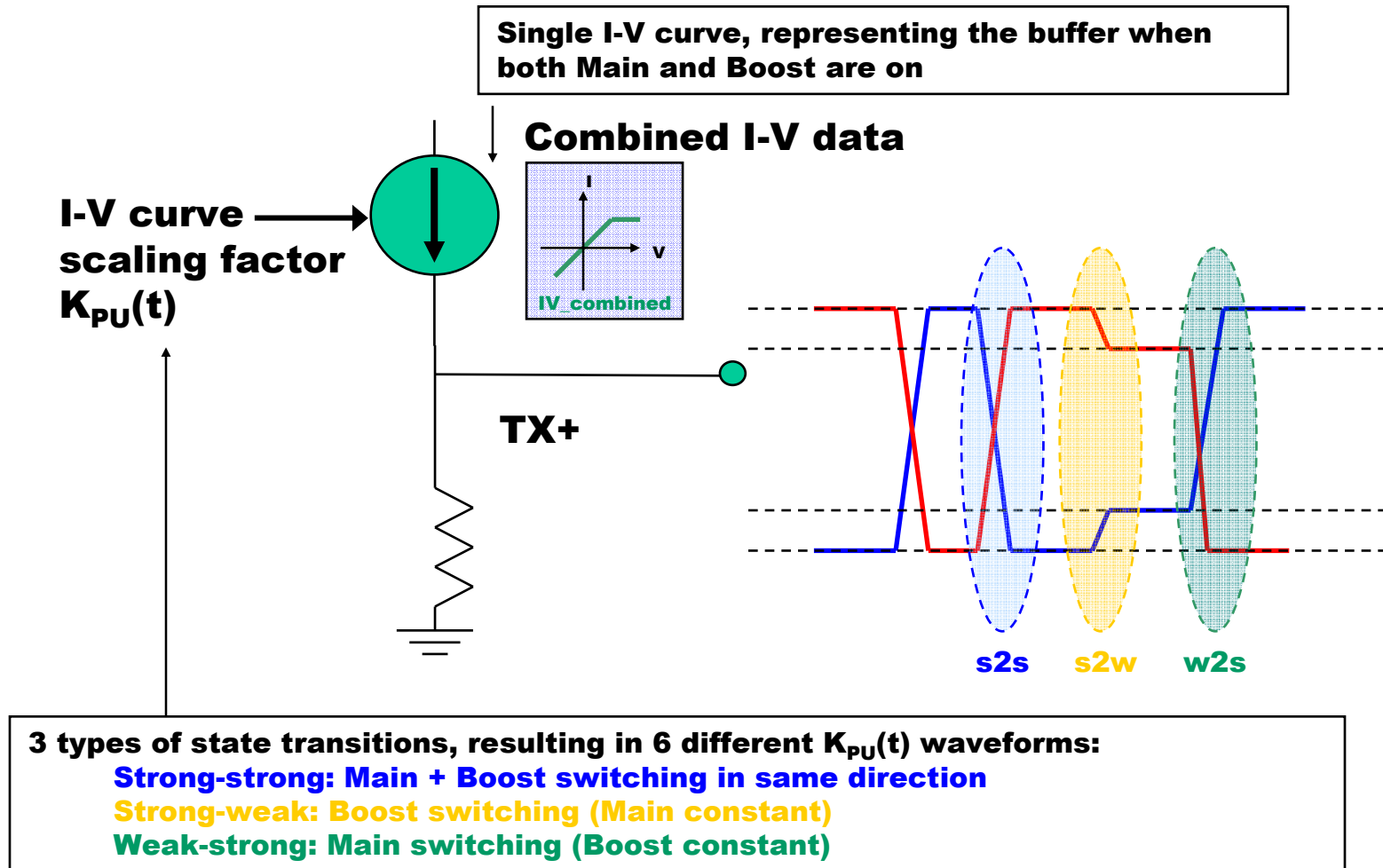


This simulation uses two separate VHDL-AMS models representing the “Main” and “Boost” blocks, in which the C_comp compensation is done independently. The reduced edge rate is a result of the two blocks loading each other.

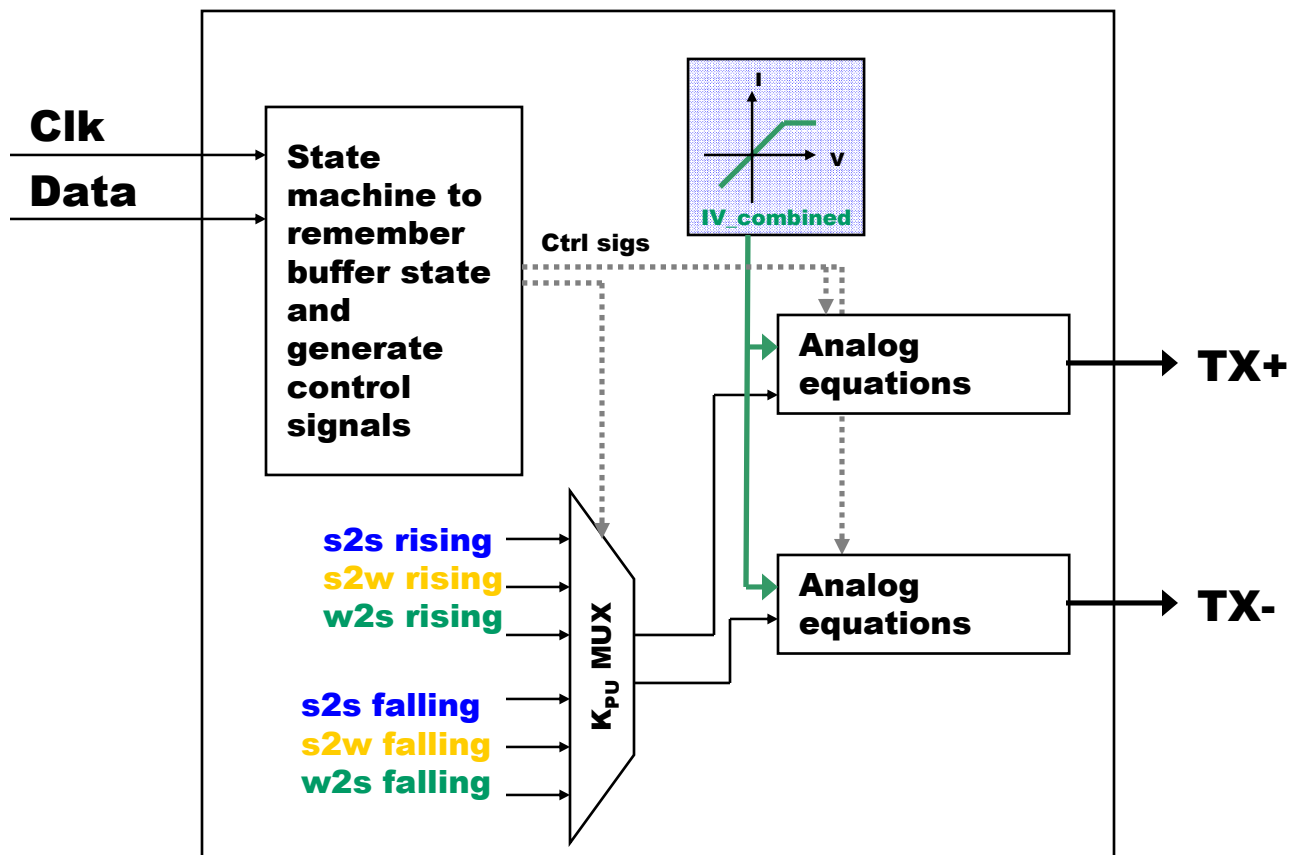
Solving this problem with a modified algorithm

- **How about combining the main and boost buffers into one single model?**
 - **Have only one I-V curve, representing the Main + Boost I-V curves**
 - **Separate V-t curves for the different transition edges**
 - Strong to strong bit
 - Strong to weak bit
 - Weak to strong bit
 - **Use *-AMS to pick the right V-t ($K_{PU}(t)$) curves to use, and scale the IV curve accordingly**
 - **No need to change the C_comp compensation equations**

Combine the Main and Boost blocks into one model



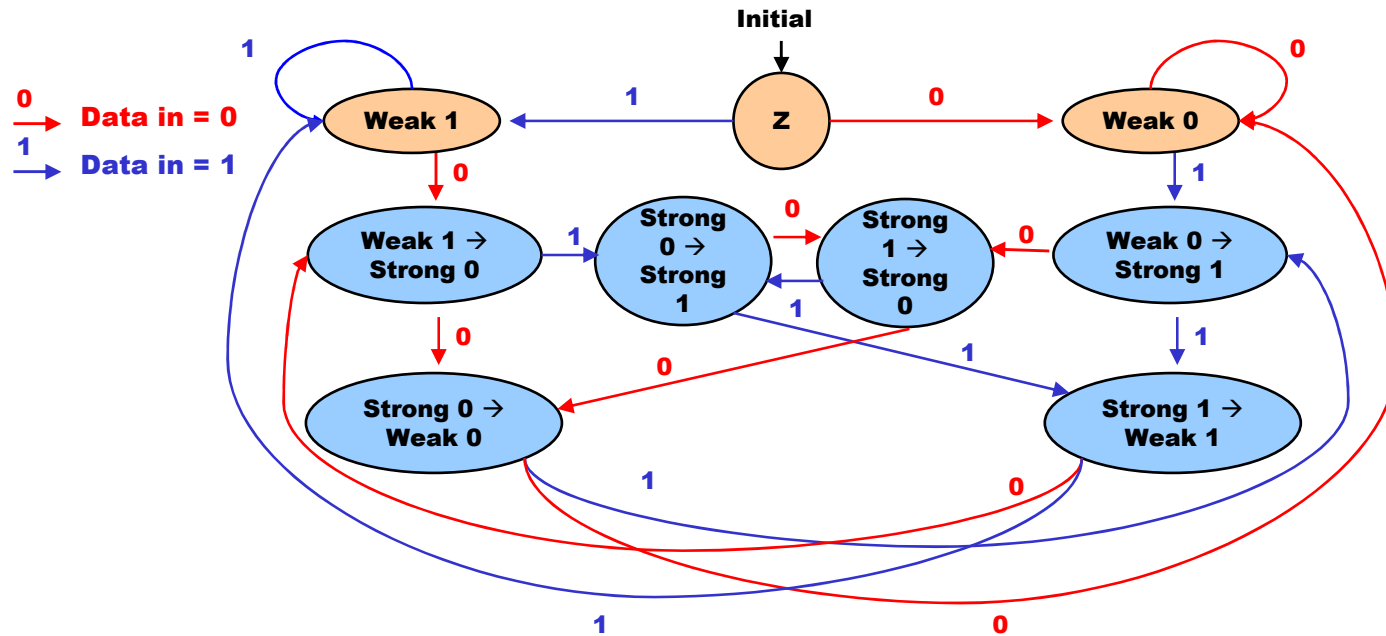
Block diagram of combined model



-- One set of analog equations

```
-----
Ipc_p_0 == -1.0 * Lookup("IV", Vpc_p_0, I_pc, V_pc); -- Power clamp eqn's
Ipu_p_0 == -1.0 * k_pu_p_0 * Lookup("IV", Vpu_p_0, I_pu, V_pu); -- Pull up eqn's
Igc_p_0 == Lookup("IV", Vgc_p_0, I_gc, V_gc); -- Ground clamp eqn's
.....
```


State machine diagram for the logic

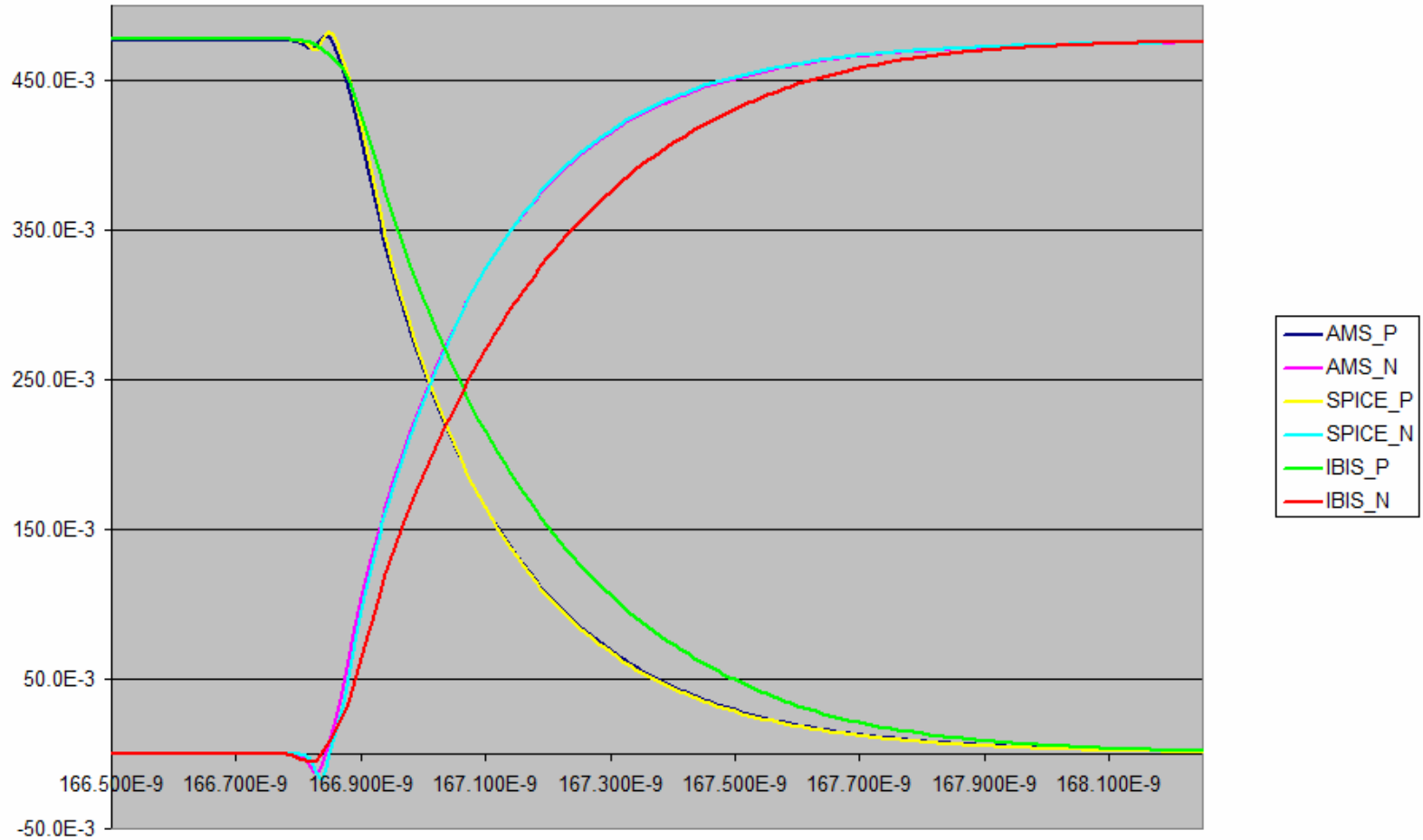


- Each blue bubble represents a buffer state transition (6 of them in total, one for each $K_{PU}(t)$ waveform)
- Orange bubbles represent no state changes
- State changes occur at clock edges

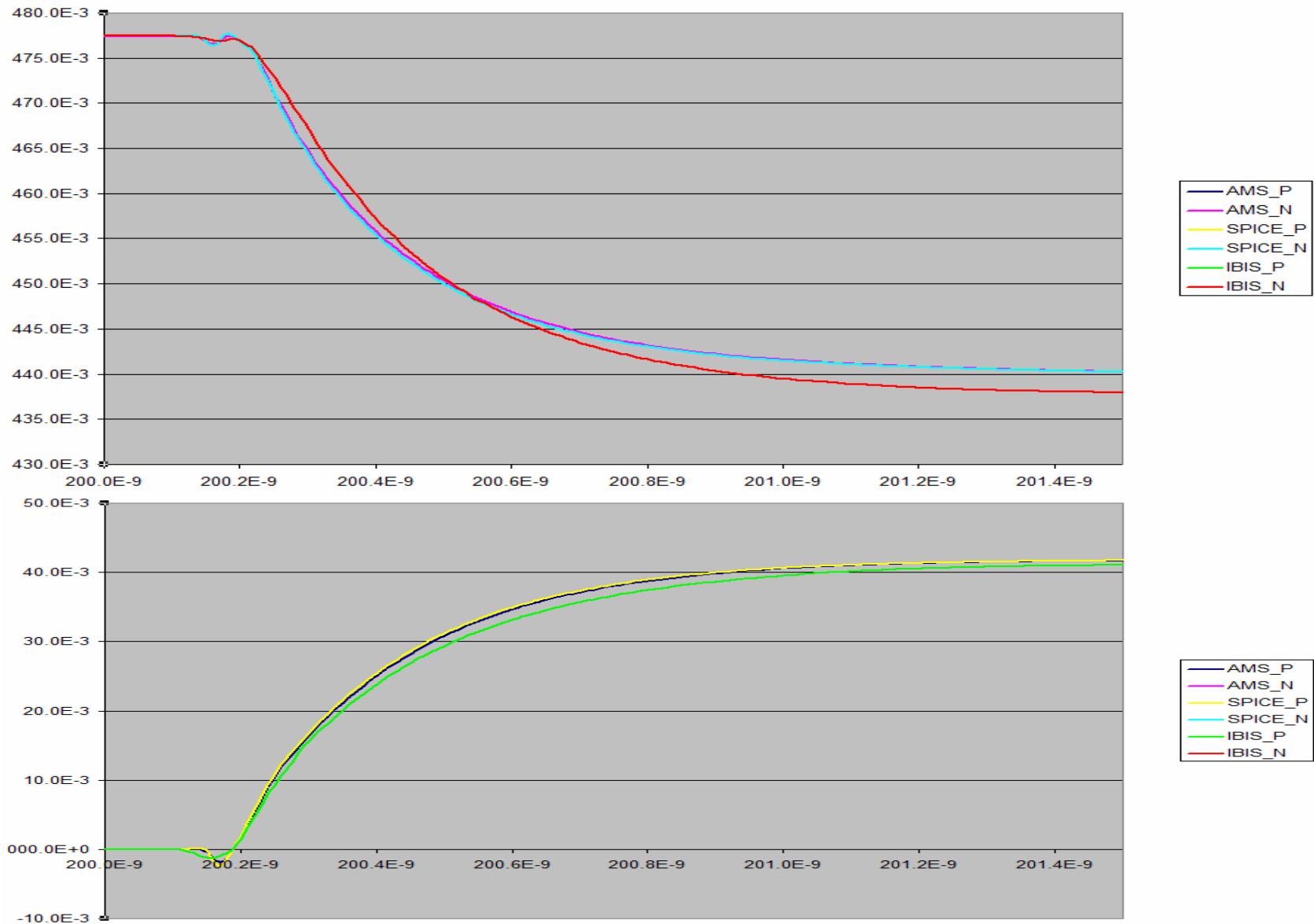
Data extraction

- **I-V curves**
 - *Only ONE I-V curve generated, for when both Main and Boost are on*
 - *Can re-use existing IBIS data (Sum Main and Boost I-V)*
 - *No need to worry about double-counting Internal terminations (between Main and Boost buffers, as in previous techniques)*
- **V-t curves**
 - *Generate V-t curves for the SIX different transition types*
 - *No need to worry about double-counting Internal terminations*
- **Same C_comp extraction methodology as before, but C_comp doesn't need to be split between buffer blocks**

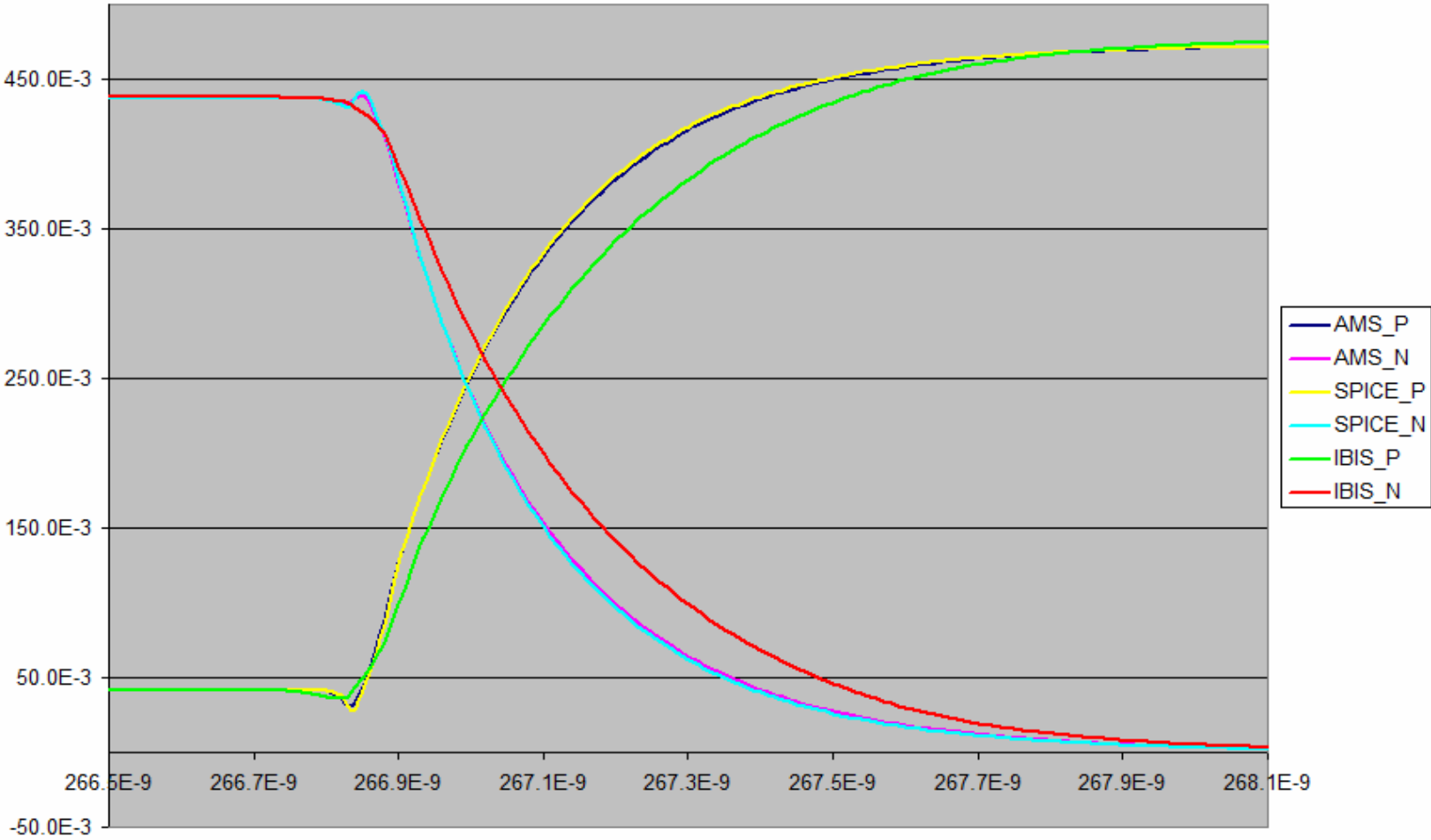
Strong bit to strong bit transition overlay



Strong bit to weak bit transition overlay



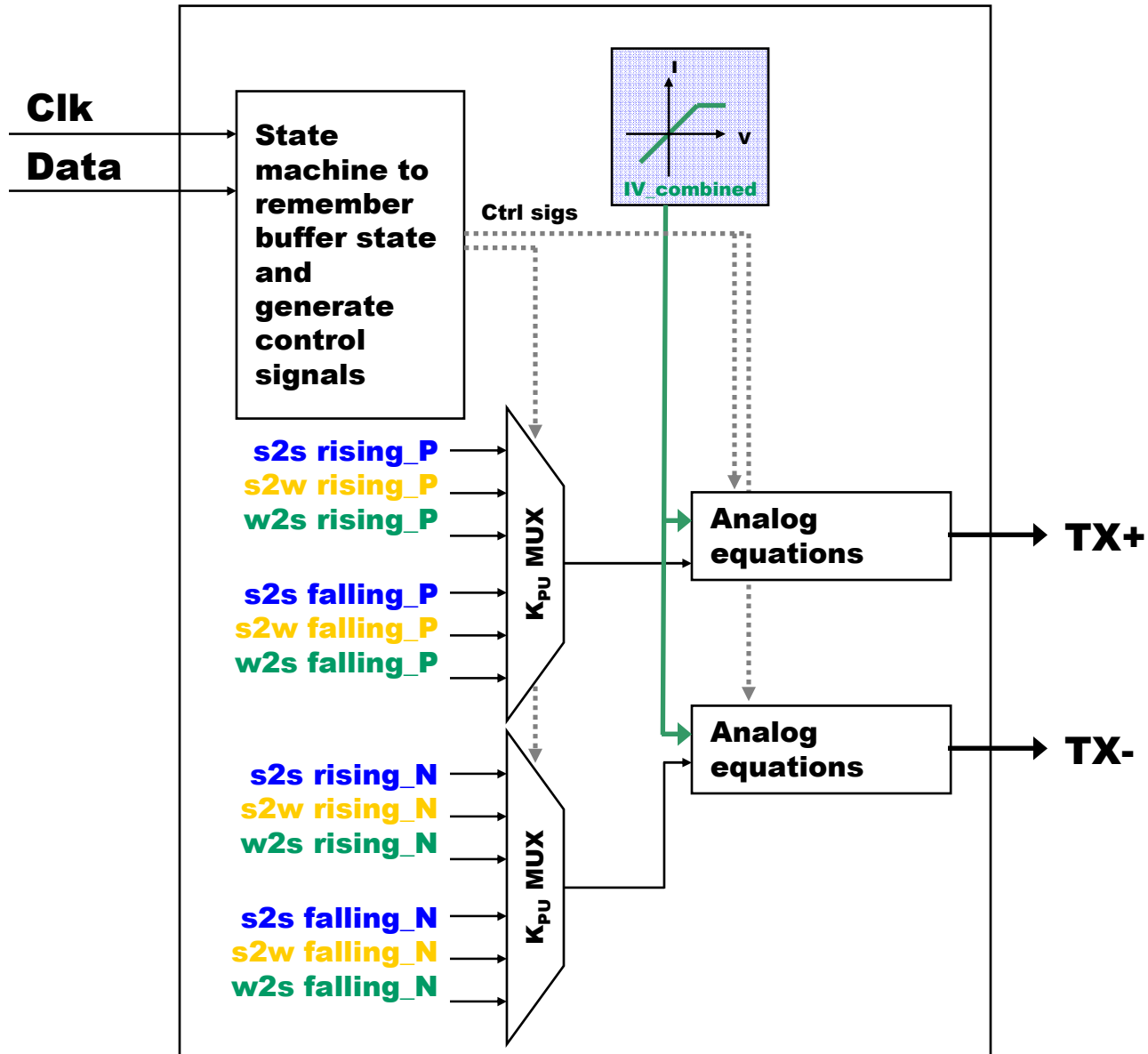
Weak bit to strong bit transition overlay



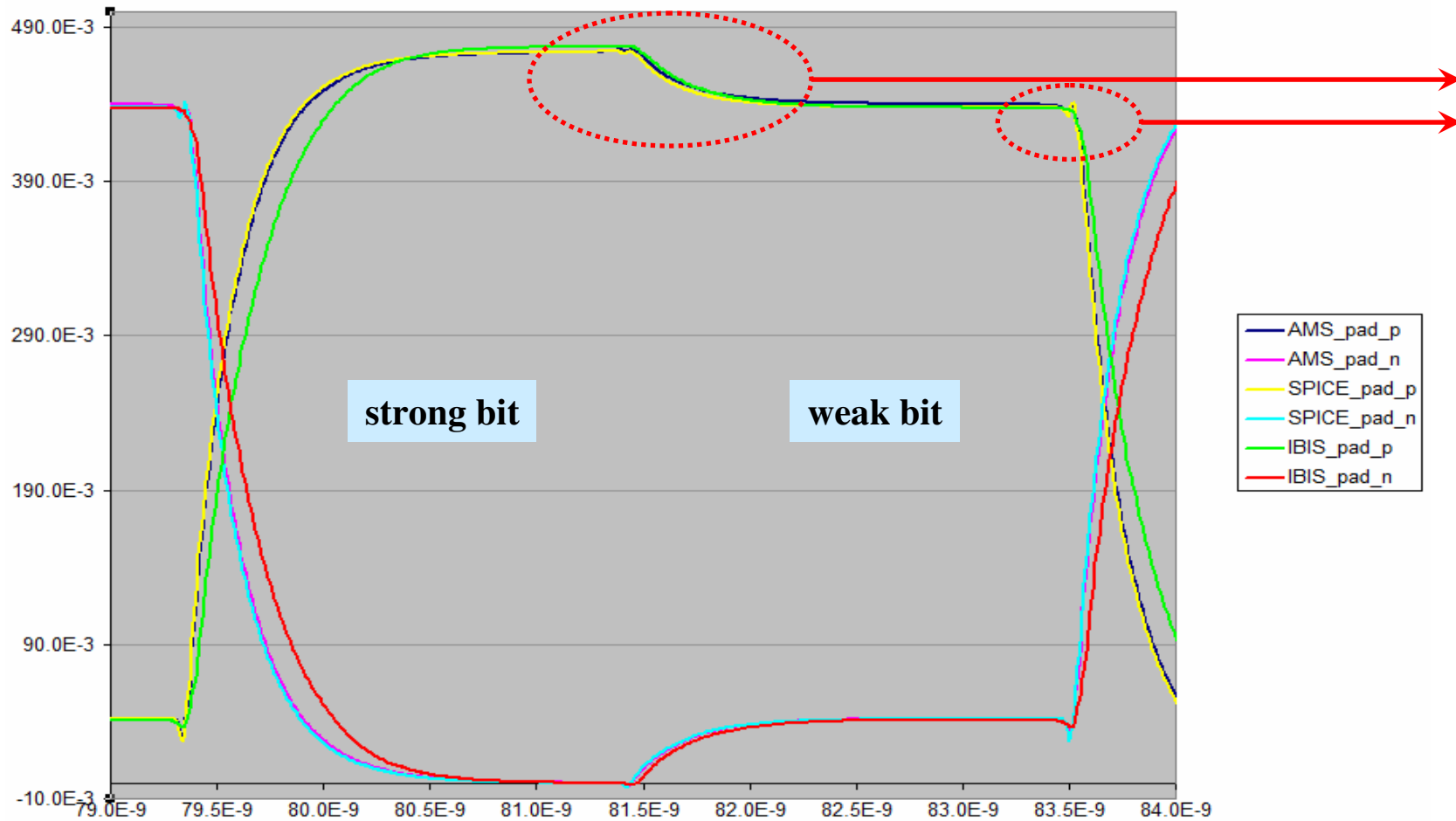
Notes on correlation results

- **Excellent match between SPICE and *-AMS model on all transitions**
 - No tweaking of the I-V & V-t curves and C_comp was necessary
 - Original C_comp compensation algorithm can still be used
 - <http://www.eda.org/pub/ibis/summits/jun03b/muranyi1.pdf> (pg. 9)
 - This *-AMS model assumes a perfectly symmetric differential buffer in which the V-t characteristics are identical for the P and N outputs
 - A small change in the code can account for the asymmetry effects also (next page)
- **However, this was done with the clock slowed down, such that the V-t curves have settled**
 - In this case, clock was slowed down from 480 MHz to 30 MHz
 - At full speed, some “switching into an unfinished edge” exists
- **Effects, such as switching into an unfinished edge, or data pattern dependent behaviors are not addressed in this presentation**

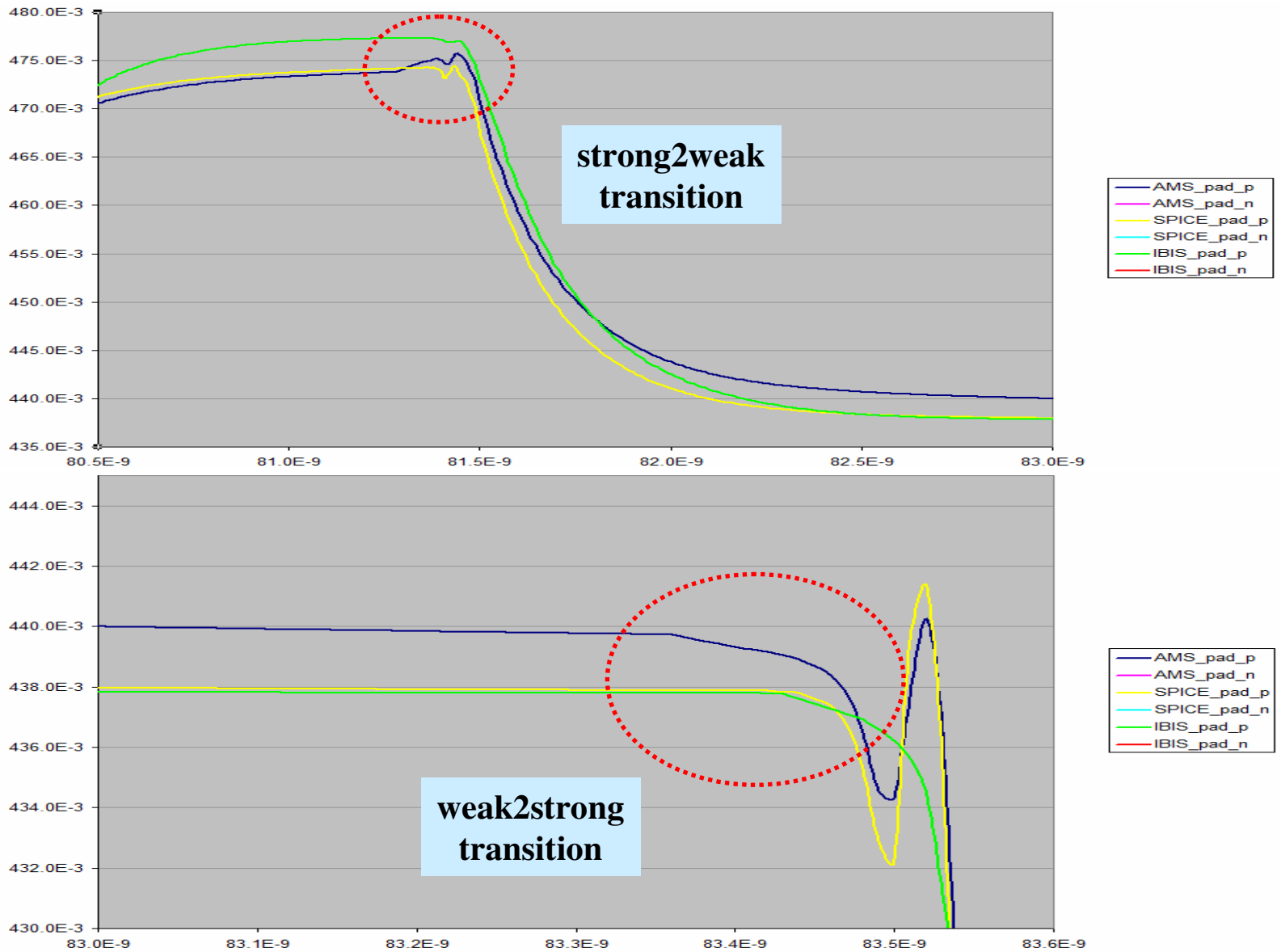
Block diagram with asymmetric differential capabilities



Simulation results at full speed (480MHz)



Details reveal some discontinuities due to unfinished edge



Conclusions

- **This study complements and completes the initial work:**
<http://www.eda.org/pub/ibis/summits/apr04/muranyi.zip>
- **The VHDL-AMS model of this presentation simulates ~2.5x faster than the model developed above**
- **This model can also include the full differential buffer characteristics, discussed at:**
<http://www.eda.org/pub/ibis/summits/oct03/muranyi.pdf>
- **Data required for this new approach**
 - I-V curve is obtained for Main + Boost driving together
 - V-t curves need to be to be generated for each switching edge
 - C_comp, measured as usual for the complete buffer
- **Next steps**
 - Solve switching into an unfinished edge problem
 - Add data pattern dependent behavior effects
 - Add frequency and/or voltage dependent C_comp
 - Test with other interfaces